

Amendments to the Specification

Please amend the specification as follows:

On page 6, between lines 23 and 24, insert:

Fig. 2G is a diagrammatic cross-section similar to Fig. 2F, showing a variation of the semiconductor structure.

Amend the paragraph spanning pages 20 and 21 as follows:

In Fig. 2E, a permanent dielectric 36 is deposited over the patterned layer of sacrificial material 30 with the metal inlay 34. The permanent dielectric 36 is deposited as a solid layer and covers the sacrificial layer 30 and at least the tops of the metal leads 34. The permanent dielectric layer may be planarized before or after removal of the sacrificial material. The permanent dielectric layer, for example, may be silicon dioxide, polyimide or other material. The permanent dielectric layer may be deposited by spin coating, spray coating or meniscus coating (typically using the sacrificial material dissolved in a solvent), chemical vapor deposition, plasma enhanced chemical vapor deposition, sol-gel process, or other method. As seen in Fig. 2E, the metal layer can be conveniently formed with a height less than the height of the adjacent sacrificial material. As will be appreciated, this will result in air gaps that extend above the tops of the metal leads, as is desirable to reduce capacitive coupling. Also, the substrate could have trenches formed therein in a pattern corresponding to the pattern of the sacrificial material, so that the resultant air gaps will extend below the metal leads located on lands on the substrate between the trenches, as illustrated in Fig. 2G.